FORM PTO-1449  U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			ATTY. DOCKET NO. ELM-1 Cont. 10	APPLICATION NO. 10/700,429	
INFORMATION DISCLOSURE				APPLICANT Glenn J. Leedy FILING DATE November 3, 2003	CONFIRMATION NO. 5639 GROUP 3729
STATEMENT BY APPLICANT					
4h	JP 02-082564	03/1990	Japan		ABST
	JP 04-083371	03/1992	Japan		ABST
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EXAMINER

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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through ditation if not conformance and not considered. Include copy of this form with next communication to applicant.